

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	+20 -16	V
Continuous Drain Current (Note 5)	I _D	T _A = +25°C	22
		T _A = +100°C	16
Continuous Drain Current (Note 6)	I _D	T _C = +25°C	145
		T _C = +100°C	103
Maximum Continuous Body Diode Forward Current	I _S	100	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	180	A
Avalanche Current, L=0.3mH	I _{AS}	27	A
Avalanche Energy, L=0.3mH	E _{AS}	110	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation	P _D	136	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	47	°C/W
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	1.1	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 24V, V _{GS} = 0V
Zero Gate Voltage Drain Current (Note 8)	I _{DSS}	—	—	10	µA	V _{DS} = 24V, V _{GS} = 0V T _J = +125°C
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = +20V, V _{DS} = 0V V _{GS} = -16V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1	1.6	3	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	3.3	3.8	mΩ	V _{GS} = 10V, I _D = 20A
		—	5	6		V _{GS} = 4.5V, I _D = 7A
Diode Forward Voltage	V _{SD}	—	0.70	1	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS						
Input Capacitance (Note 8)	C _{ISS}	—	2370	—	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1MHz
Output Capacitance (Note 8)	C _{OSS}	—	1360	—		
Reverse Transfer Capacitance (Note 8)	C _{RSS}	—	240	—		
Gate Resistance	R _g	0.14	0.7	1.75	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
SWITCHING CHARACTERISTICS (Note 8)						
Total Gate Charge (V _{GS} = 10V)	Q _g	—	43.7	—	nC	V _{DS} = 15V, I _D = 20A
Gate-Source Charge	Q _{gs}	—	6.9	—		
Gate-Drain Charge	Q _{gd}	—	8	—		
Turn-On Delay Time	t _{D(ON)}	—	6.2	—	ns	V _{DD} = 15V, V _{GS} = 10V, R _G = 3Ω, R _L = 0.75Ω
Turn-On Rise Time	t _R	—	4.2	—		
Turn-Off Delay Time	t _{D(OFF)}	—	21	—		
Turn-Off Fall Time	t _F	—	8	—		
Body Diode Reverse Recovery Time	t _{RR}	—	25	—	ns	I _F = 15A, dI/dt = 500A/µs
Body Diode Reverse Recovery Charge	Q _{RR}	—	37	—	nC	

- Notes:
- Device mounted with exposed drain pad on 25mm by 25mm 2oz copper on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady state.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

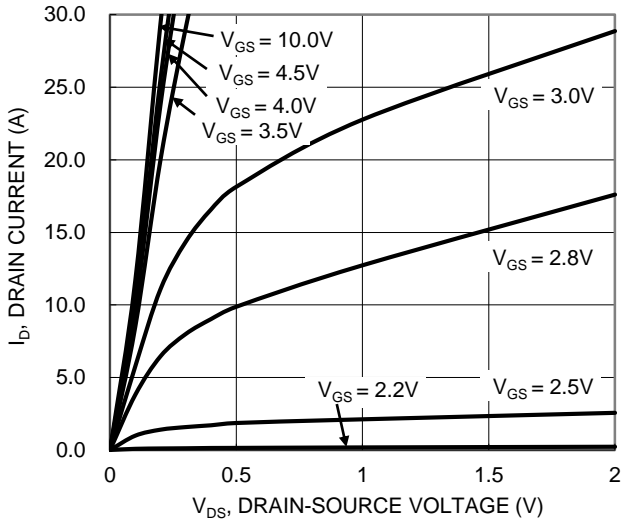


Figure 1. Typical Output Characteristic

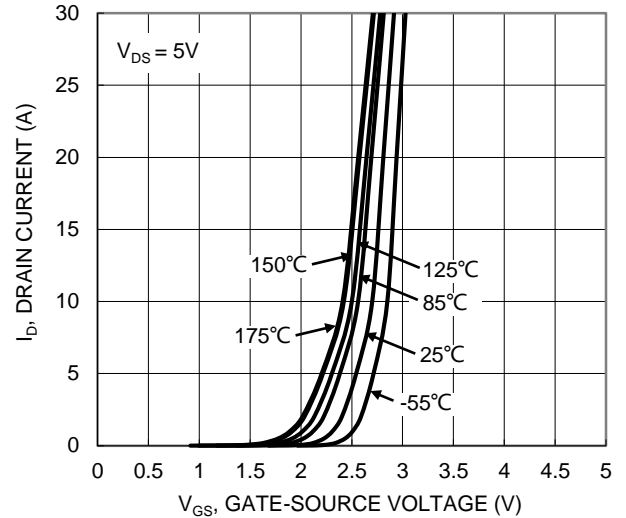


Figure 2. Typical Transfer Characteristic

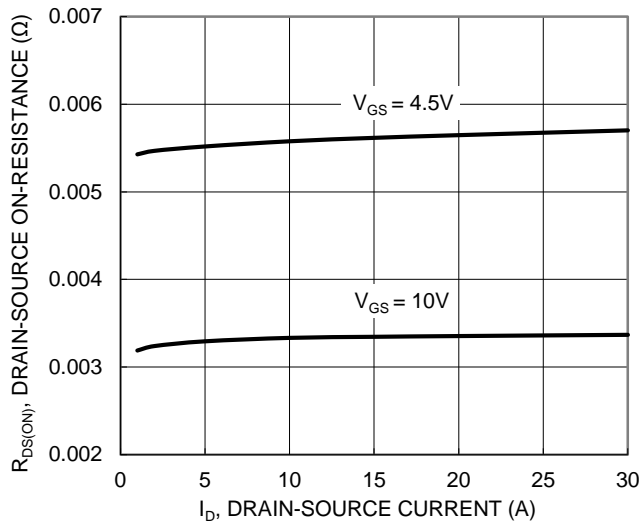


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

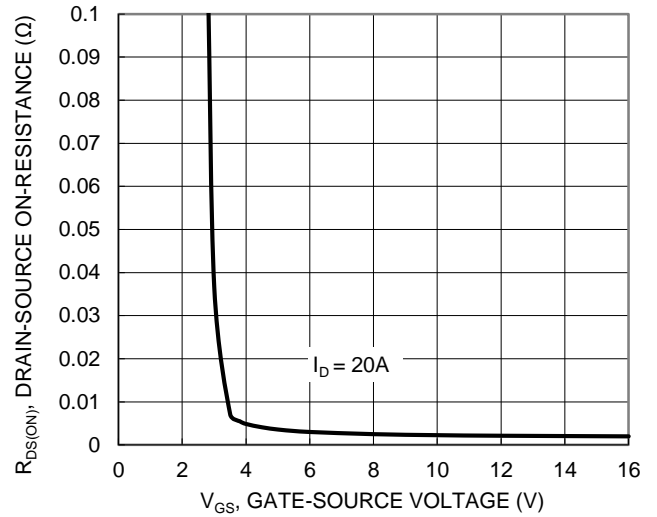


Figure 4. Typical Transfer Characteristic

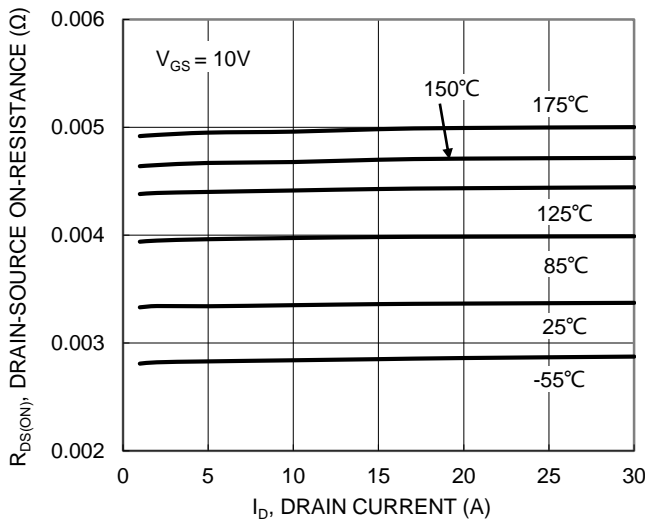


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

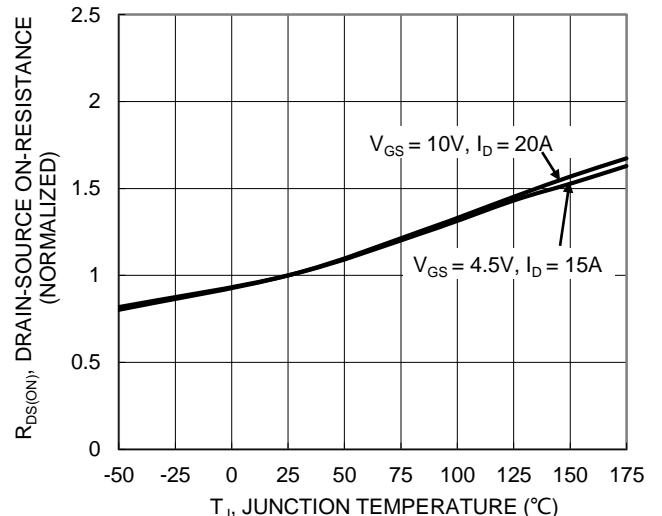


Figure 6. On-Resistance Variation with Junction Temperature

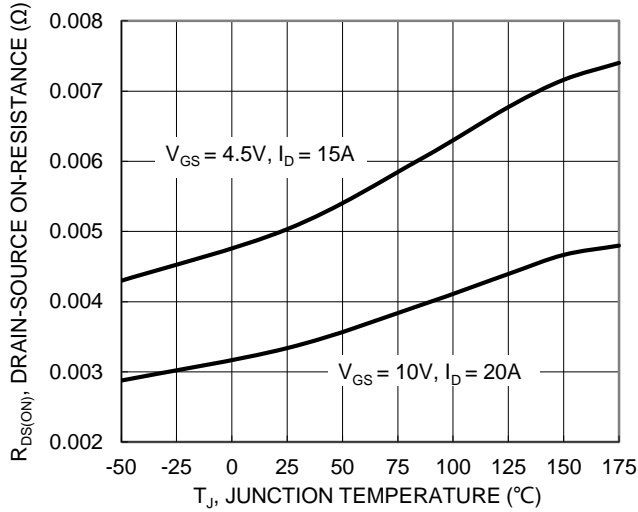


Figure 7. On-Resistance Variation with Junction Temperature

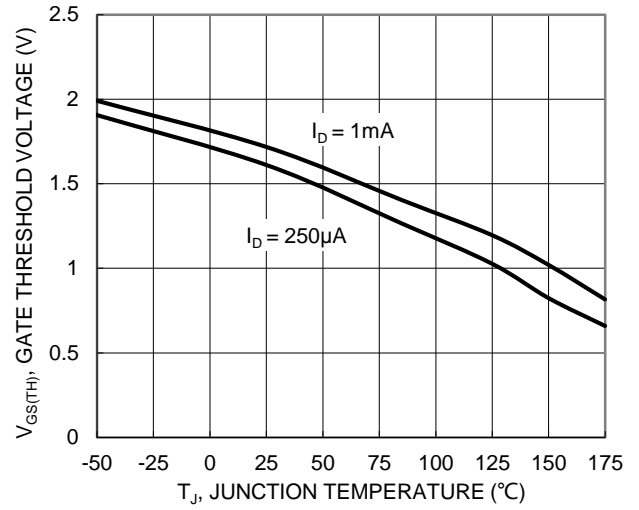


Figure 8. Gate Threshold Variation vs. Junction Temperature

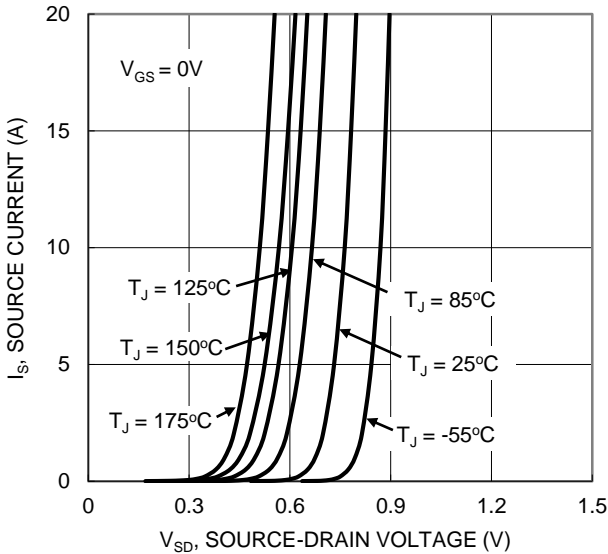


Figure 9. Diode Forward Voltage vs. Current

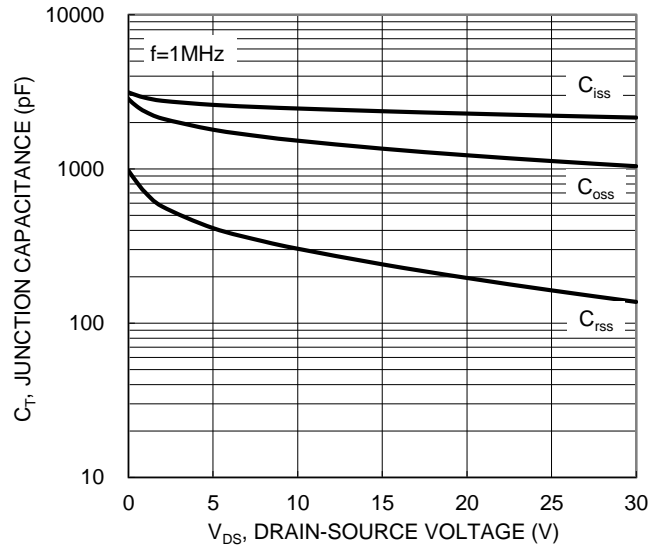


Figure 10. Typical Junction Capacitance

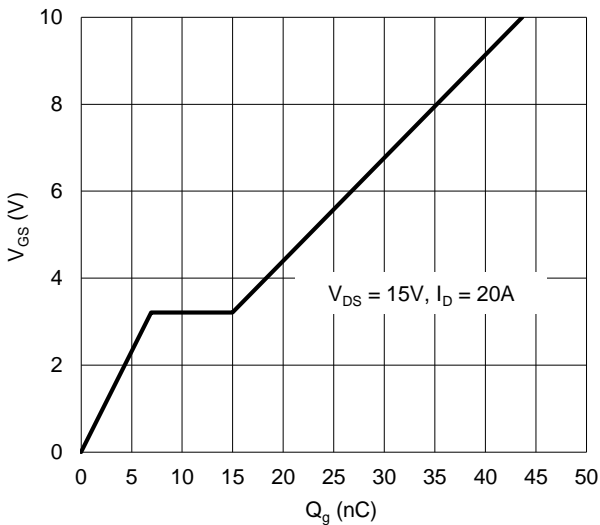


Figure 11. Gate Charge

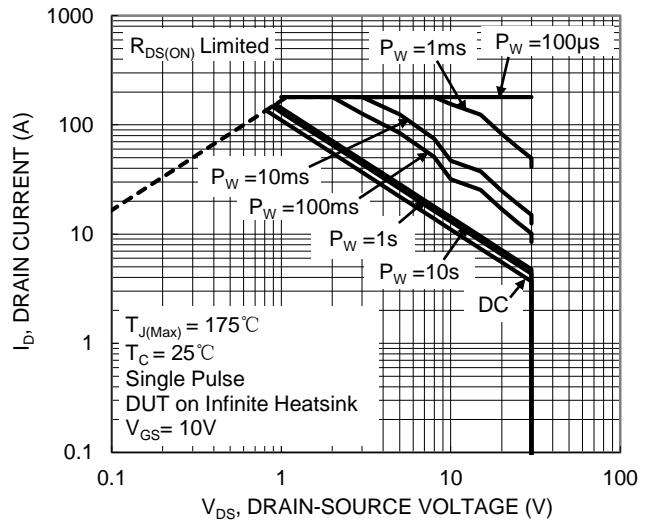


Figure 12. SOA, Safe Operation Area

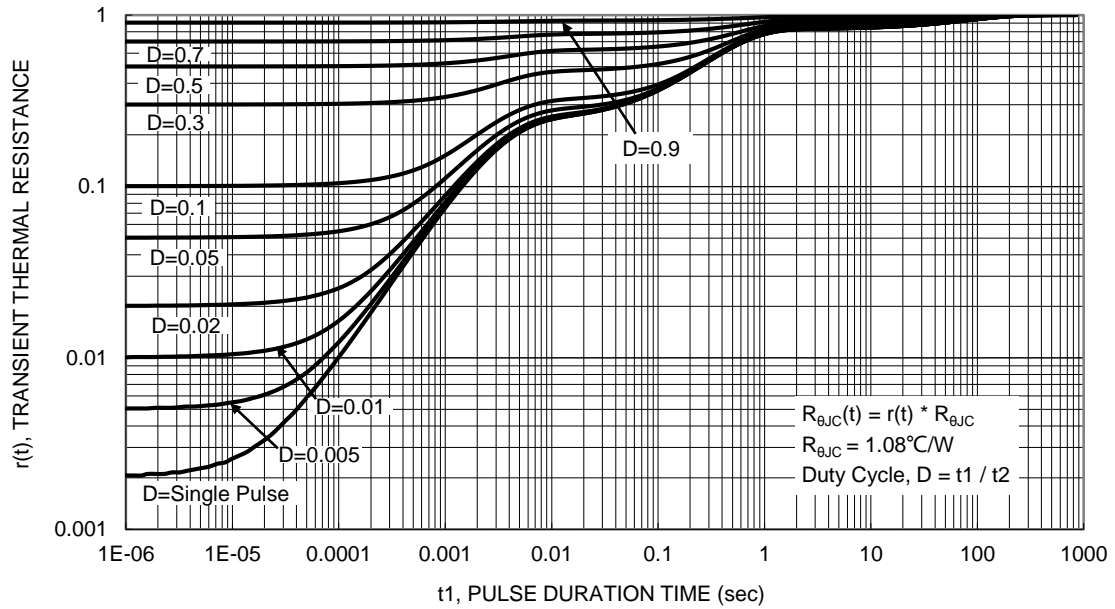
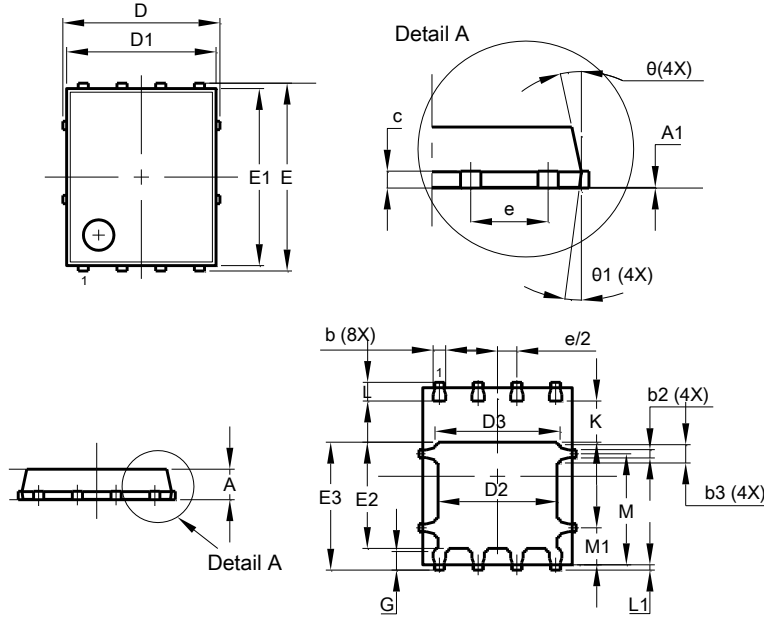


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8

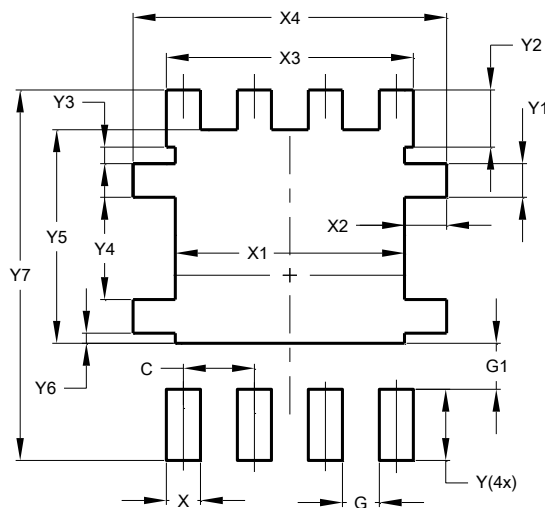


PowerDI5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	-
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	-	-
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

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